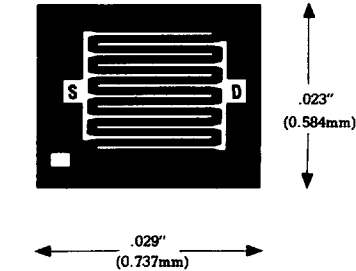


PRODUCT CATALOG

P-CHANNEL JUNCTION FET

CHIP NUMBER

FP7.3



Die Size: 29 x 23 (mils)
0.737 x 0.584(mm)
3 x 3 (mils)
Pad Size: 0.076 x 0.076(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

- It is advisable that:
- a) the die be eutectically mounted with gold silicon preform 98/2%.
 - b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

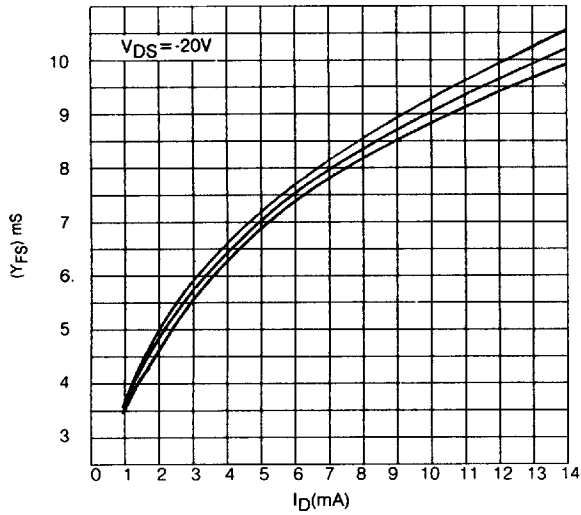
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	25	40	50	V	VDS = 0, IG = 1μA
IDSS	-5.0	-30	-120	mA	VDS = -15V, VGS = 0
gfs		10		mmho	VDS = -15V, VGS, = 0
IGSS		50	500	pA	VGS = 20V, VDS = 0
rDS	40	100	200	Ω	VDS = 100mV, VGS = 0
VGS(off)	1.0	4.0	10	V	VDS = -15V, ID = 1nA
Crss		4.5		pF	VDS = 0, VGS = 10V, f = 1MHz
Ciss		20	25	pF	VDS = -15V, VGS = 0, f = 1MHz

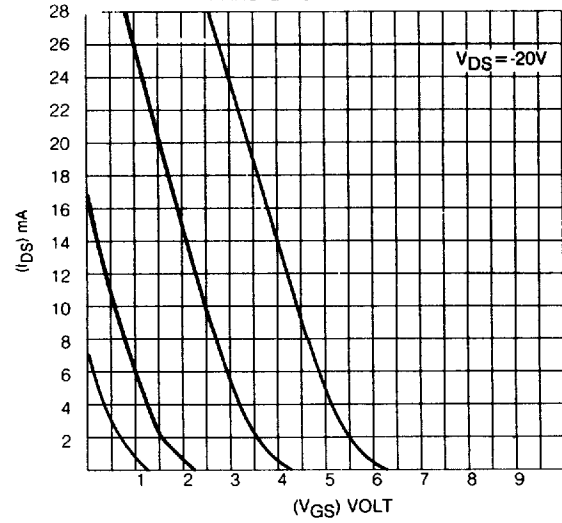
TYPICAL DEVICE TYPES: 2N5018, 2N5019, 2N5114 - 2N5116, 2N5319

CHIP TYPE FP7..3

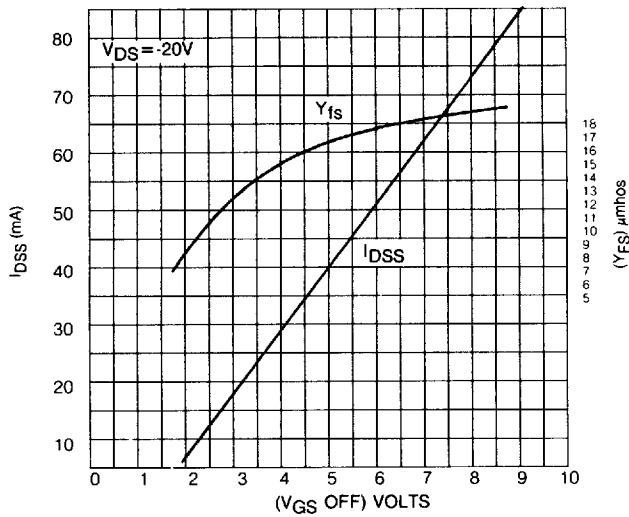
FORWARD TRANSADMITTANCE
VS. OPERATING DRAIN CURRENT



TRANSFER CHARACTERISTIC



FORWARD TRANSADMITTANCE



OUTPUT CHARACTERISTICS

